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(54) FORMATION OF RESIST PATTERN

(57)Abstract:

PURPOSE: To prevent charge up by using a conductive film of poly β -diketone as a flattening layer.

CONSTITUTION: The poly β -diketone layer is formed as the flattening layer on a semiconductor substrate, for example, Al/Si substrate in formation of a resist pattern for which multi-layered resist layers having conductive films are used under a resist layer. After the resist layer is then formed, the layer is patterned. Since the poly β -diketone has conductivity, the charge stagnating in the resist on the poly β -diketone layer flows through the poly β -diketone to the semiconductor substrate. The charge up is thereby prevented.

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